INFORMATION DISCLOSURE CITATION
PTO-1449

Customer Number	Attorney's Dkt No.	Application No.
26615	H1492	10/653,105
	Applicant(s) Bin Yu et al.	
	Filing Date September 3, 2003	Group 2811 ~~Unassigned~~

U.S. PATENT DOCUMENTS

Examiner's Initials	Patent No.	Date	Name	Class	Subclass	Filing Date

FOREIGN PATENT DOCUMENTS

Examiner's Initials	Patent No.	Date	Country	Class	Subclass	Translation Yes	Translation No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

VU	U.S. Patent Application Publication No. US 2002/0003255 A1, January 10, 2002, Usuki et al.

EXAMINER	DATE CONSIDERED
HUNG VU	08/07/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

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U.S. PATENT DOCUMENTS

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✓	4,979,014	12-18-90	Hieda et al.	357	56	08-05-88

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Examiner's Initials	Patent No.	Date	Country	Class	Subclass	Translation Yes	Translation No
✓	EP 0 623 963 A1	11-09-94	Europe	—	—		X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	PCT International Search Report, April 8, 2004, 3 pages.

EXAMINER	DATE CONSIDERED
HUNG VU	08/07/04

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INFORMATION DISCLOSURE CITATION PTO-1449	Customer Number: 26615	ATTORNEY'S DKT NO. H1492	APPLICATION NO. ~~Unassigned~~ 10/653,105
		APPLICANT(S) Bin Yu et al.	
		FILING DATE September 3, 2003	GROUP 2811 ~~Unassigned~~

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VH	6,525,403 B2	02-25-03	Inaba et al.	257	618	09-24-01/
VH	6,433,609 B1	08-13-02	Voldman	327	313	11-19-01

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

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VH	Digh Hisamoto et al.: "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
	Yang-Kyu Choi et al.: "Sub-20nm CMOS Fin FET Technologies," 2001 IEEE, IEDM, Pages 421-424.
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	Co-pending Application Serial No. 10/348,758, filed January 23, 2003, entitled "GERMANIUM MOSFET DEVICES AND METHODS FOR MAKING SAME," 22 page specification, 29 sheets of drawings.
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	Co-pending Application Serial No. 10/348,911, filed January 23, 2003, entitled "TRI-GATE AND GATE AROUND MOSFET DEVICES AND METHODS FOR MAKING SAME," 17 page specification, 18 sheets of drawings.
	U.S. Patent Application Publication No. US 2003/0113970 A1; June 19, 2003; Fried et al.
VH	U.S. Patent Application Publication No. US 2003/0042531 A1; March 6, 2003; Lee et al.

EXAMINER	HUNG VU	DATE CONSIDERED	08/07/04

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